Form ation of a Quasi-Periodic Copper Thin Film

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We have synthesized a thin Im of copper with a quasi-periodic structure by the adsorption of copper atom s on the ve-fold surface of the icosahedral quasicrystal A HP d-M n at room tem perature. The quasi-periodicity of the thin Im is manifested in low energy electronic di raction (LEED) measurements and in the existence of Fibonacci relationships between rows of copper atom s imaged using scanning tunneling microscopy (STM). These indiges demonstrate the feasibility of single-element quasi-periodic thin Im formation using quasicrystals as tem plates.

C opper is one of the oldest elem ents known to mankind and it crystallizes in a face-centred cubic structure. Quasicrystals are a relatively new form of matter, rst reported in 1984¹, and are bi- and trim etallic alloys with long-range order but no translational symmetry. In the course of investigations aim ed at understanding the interactions between quasicrystal surfaces and adsorbed atom ic and m olecular species², we have discovered that the adsorption of Cu on the ve-fold surface of the icosahedral quasicrystal A HP d-M n at 300 K leads to the formation of a quasi-periodic Cu thin lm. The quasiperiodic structure of the thin lm is manifested in low energy electronic di raction (LEED) measurements and in the existence of Fibonacci relationships between rows of Cu atom s on the surface in aged using scanning tunneling m icroscopy (STM). The ability to synthesise such single-elem ent quasi-periodic thin Im swill facilitate the study of the relationship between quasi-periodicity and physical properties and enable the probing of the transition from two-dimensional (2D) to three-dimensional (3D) electronic properties in a quasi-periodic m aterial.

The starting point in these investigations is the preparation of high quality clean surfaces of A HP d-M n with large at terraces (m icrons in size) and low surface corrugation in an ultra-high-vacuum (UHV) environment. The methodology for the preparation of these surfaces has been previously described in detail^{3,4} and consists of ex-situ polishing followed by several cycles of ion sputtering (1 hour) and annealing to 940 K (4 hours) with a cum ulative annealtine of 20 hours. Surface preparation is facilitated using LEED to establish the degree of surface ordering and A uger electron spectroscopy (AES) to check for contam ination (and later to monitor C u deposition). Surfaces prepared in this manner have been show n to be essentially ideal term inations of the bulk quasicrystal structure^{3,5}, and the 2D structure of these surfaces has been described as a Fibonacci pentagrid⁶, with the ve principal sym m etry axes evident in the arrangem ent of the dom inant structural motifs. This is illustrated in Fig. 1(a) which shows a high resolution STM image of a smallarea (10 nm x 10 nm) of such a surface. Several groupings of atom swith ve-fold and ten-fold symmetry are evident. The dark ve-fold stars are Bergm an clusters (a basic structural entity of this type of quasicrystal) which have been truncated in the surface form ation process⁴. White lines drawn on the gure join identical positions on the dark ve-fold stars; the separations between the lines are of two lengths L = 0.74 0.02 nm and S = 0.46 0.02 nm, whose ratio is within experimental error equal to the golden m ean ; [is the irrational num ber expected for the ratio of the two basic units of the Fibonacci sequence [=(5+1)=2=1:618:::]. Furtherm ore the arrangem ent of these line separations (reading from bottom to top) LSLLSL forms a segment of the Fibonacci sequence.

Deposition of Cu atom s on the surface was achieved using a simple evaporation source consisting of a tantalum lament which was wrapped around a sample of pure Cu. The lament was thoroughly degassed before evaporation and the evaporation ux was found to be very consistent under constant conditions of the control parameters. The experiments were conducted using a Cu ux of 45 0.2×10^{-2} m onolayers s⁻¹ as determined by measuring the fractional area of the surface covered with successive Cu depositions. The sample was at room temperature during deposition and measurement.

Figure 2 gives an overview of the growth of Cu on the surface at room temperature for increasing Cu coverage. Under the above deposition conditions the growth of Cu on the A l-P d-M n surface is observed to proceed in a layerby-layer manner. The step height from layer to layer is 0:19 0:01 nm. For sub-monolayer coverages (Fig. 2 (a)) Cu islands form on the surface and as adsorption continues the second layer is observed to begin growing when the rst layer is 90 5 % complete. For layers 1 to 4 the Cu atom swithin the layers are observed to self-organise into small domains within which there is a developing pattern of one-dimensional rows (Fig 2 (b)). From layers 5 to 8 a very well-developed row structure is observed (Fig. 2 (c)). From layer 9 the e ect of layer growth before previous layer completion becomes more marked as shown in Fig. 2 (d); this results in a diminishing domain size and in the simultaneous existence of many incomplete layers at the surface. The row structure persists in these layers. The results were reproduced several times and the growth was monitored up to the 25th. layer.

Fig. 3(a) is a 40nm x 40 nm in age taken during the growth of the 6th layer. This in age reveals several intriguing details. The islands have sharp edges where the border is a single row. A plausible explanation for the growth mechanism is the initial adsorption of Cu on top of a growing layer, followed by di usion of the adsorbed atom s along the Cu rows and subsequent attachment at the end of each row. The rows them selves appear in ve orientations, with the angles made by intersections of rows in the same layer corresponding to the internal angles of a pentagon. The intersections between rows are of two types. Two sets of rows can meet at vertex points, where the end of each row in one direction meets the end of another at an angle of 108° (the internal angle of a

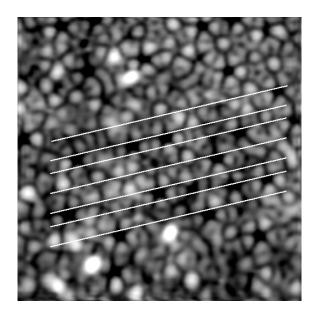


FIG.1: 10 nm x 10 nm STM image of the ve-fold surface of A Pd-Mn. The lines join identical positions on the dark ve-fold stars; the separations between the lines are of two lengths L = 0:74 0:02 nm and S = 0:46 0:02 nm, whose ratio is within experim ental error equal to the golden mean ; furtherm ore the arrangement of these line separations (from bottom to top) LSLLSL forms a segment of the Fibonacci sequence.

pentagon). A lternatively the rows in one direction intersect a single row at an angle of 72° . The rows do not form a periodic structure.

The corrugation across the row s is measured at 0.025 0.005 nm using STM. The atom ic structure within the rows is not resolved in these experiments; this could be an indication of a large vibrational amplitude along the rows; alternatively it could reject a low corrugation in electronic density along the rows. The fact that the LEED pattern shows discrete spots is indicative of longrange order both within and across domains and along the rows them selves. The row directions are also observed to be correlated from layer to layer, indicating that each layer acts as a tem plate for the subsequent one in the growth process.

The inter-row distances form aperiodic sequences having long and short separations. This is illustrated in Figure 4 which shows a 10 nm x 10 nm image of the surface during form ation of the 6th layer. There are some vacancy defects in the rows them selves. Nevertheless sequences of rows having S and L separations are visible. The average spacings are measured at 0:45 0:02 nm and L = 0.73 0.03 nm. The ratio of these numbers equals the golden mean within experimental error. Two such sequences (SLLSLSL, reading from bottom to top) are indicated on this gure, on rows which meet at vertex points. This indicates that the same sequencing information is common to both sets of rows. The coherence length of the row structures appears to be determ ined by the dom ain walls which arise during the growth process. The close m atch of these row spacings in the Cu structure with those illustrated for the clean surfaces (Figure

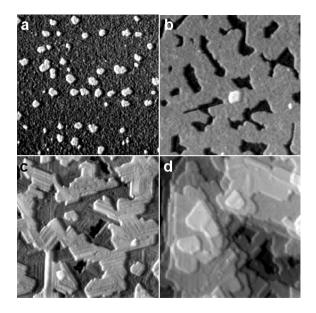


FIG.2: (a) 50 nm x 50 nm STM snapshots of the ve-fold surface of A PPd-M n during the growth of the Cu thin lm. (a) 0.09 layers of Cu, (b) 3.8 layers, (c) 5.5 layers, (d) 11.7 layers.

1) indicate that the clean surfaces acts as a tem plate for the ordered grow th of the C u atom s.

The LEED pattern characteristic of this layered row structure is shown in Fig. 3 (b). The pattern has ten-fold sym metric rings of spots whose distances from the central spot (hidden by the electron gun in the Figure) exhibit a -scaling relationship. From layers 9 to 20, with the sim ultaneous grow th ofm ultiple layers, the LEED pattern becomes streaky and di use and eventually degrades and disappears by the 25th layer. This is consistent with the dim inishing dom ain size.

Upon annealing to 570 K, STM im ages (not shown)

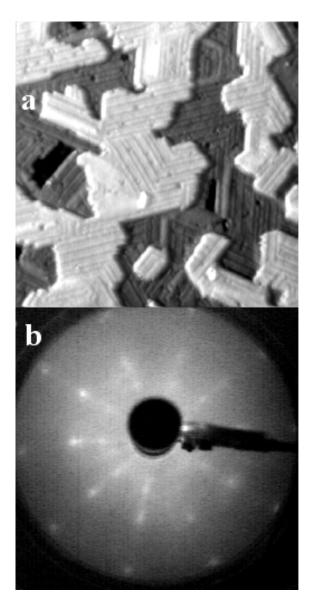


FIG.3: (a) 40 nm x 40 nm STM in age of the ve-fold surface of A HPd-M n after deposition of 5.5 M L of Cu. (b) LEED pattern (beam energy 50 eV) corresponding to this phase. The relationships between spot positions are indicative of - scaling within experimental error.

reveal that the Cu thin lm undergoes an irreversible transform ation to a cubic structure Cu with ve dom ains rotated from each other by 72°. The LEED pattern associated with this phase, although 10-fold symmetric, no longer has the -scaling relationships in the distances of the di raction spots. The dom ain boundaries of this phase are decorated with excess Cu atom s. Flashing the sample to 660 K results in thermal desorption of the Cu lm and the clean surface LEED pattern is restored.

There has been a report of the use of these surfaces for the growth of ve-fold symmetric nanoclusters⁷ by the adsorption of sub-monolayer amounts of alum inum on A LC u-Fe. There has been a report of ordered atom ic Si and B im onolayers on quasicrystal surfaces⁸, and another report of the formation of a quasicrystalline bim etallic A u-A lalloy by deposition and subsequent annealing of a A u Im on an A LP d-M n substrate⁹. In other work, the deposition of A g at low tem perature onto to a G aA s(110) substrate followed by annealing to room tem perature was found to form a A g (111) Im with a surface quasiperiodic modulation^{10,11}. However the system described in this report is unique in that it constitutes a single elem ent quasi-periodic thin Im grown using a quasicrystal surface as a tem plate.

The quasi-periodicity of the lm, together with the one-dimensionality of the row structure, suggest the possibility of unusual vibrational and electronic properties in this system. The well-docum ented low density of electronic states at the Ferm i level in the bulk quasicrystal (the so-called pseudogap) means features in the va-

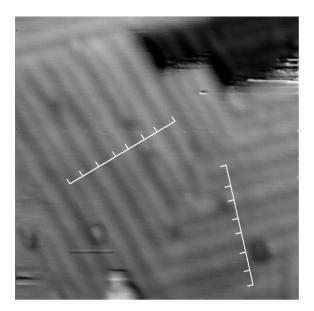


FIG.4: (a) 10 nm x 10 nm STM image of the ve-fold surface of A Pd-M n. The lines marks sequences of C u rows with spacings given by SLLSLSL (from bottom to top). The spacings are S = 0.45 0.02 nm and L = 0.73 0.03 nm. The ratio of these numbers equals the golden mean within experimental error.

lence electronic structure of the Cu lm should be readily distinguishable from those of the substrate. This system also o ers interesting possibilities for monitoring the transition from 2D to 3D electronic properties in a quasi-periodic material as the thickness of the lm is increased, and for probing the relationship between quasi-periodicity and physical properties. The surface of the lm itself has the potential to act as an adsorption tem plate for the form ation of further quasi-periodic system s. Furtherm ore we have no reason to believe that the

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Cu/AlPd-Mn system is unique; we anticipate the discovery of further aperiodic thin lm systems, with the promise of new electronic and/or magnetic properties.

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